

Silicon PNP Power Transistors

2SA885

DESCRIPTION

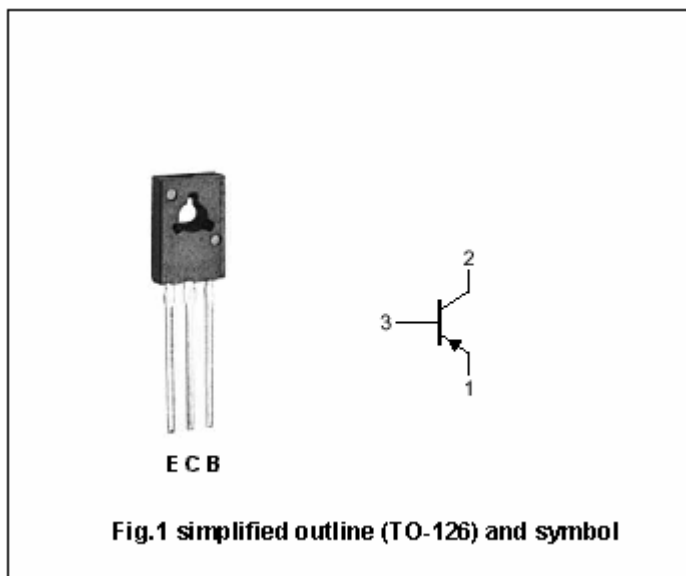
- With TO-126 package
- Complement to type 2SC1846
- Low collector-emitter saturation voltage

APPLICATIONS

- For low-frequency power amplification

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute Maximun Ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-45	V
V_{CEO}	Collector-emitter voltage	Open base	-35	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-1	A
I_{CM}	Collector current-peak		-1.5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	1.2^{*1}	W
			5^{*2}	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

Note) *1: Without heat sink

*2: With a 100 × 100 × 2 mm A1 heat sink

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-2mA; I_B=0$	-35			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-10\mu A; I_E=0$	-45			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-0.5A; I_B=-50mA$			-0.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-20V; I_E=0$			-0.1	μA
I_{CEO}	Collector cut-off current	$V_{CE}=-20V; I_B=0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-10	μA
h_{FE-1}	DC current gain	$I_C=-0.5A; V_{CE}=-10V$	85		340	
h_{FE-2}	DC current gain	$I_C=-1A; V_{CE}=-5V$	50			
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-10V; f=1MHz$		20	30	pF
f_T	Transition frequency	$I_C=50mA; V_{CB}=-10V; f=200MHz$		200		MHz

◆ h_{FE-1} Classifications

Q	R	S
85-170	120-240	170-340

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PACKAGE OUTLINE

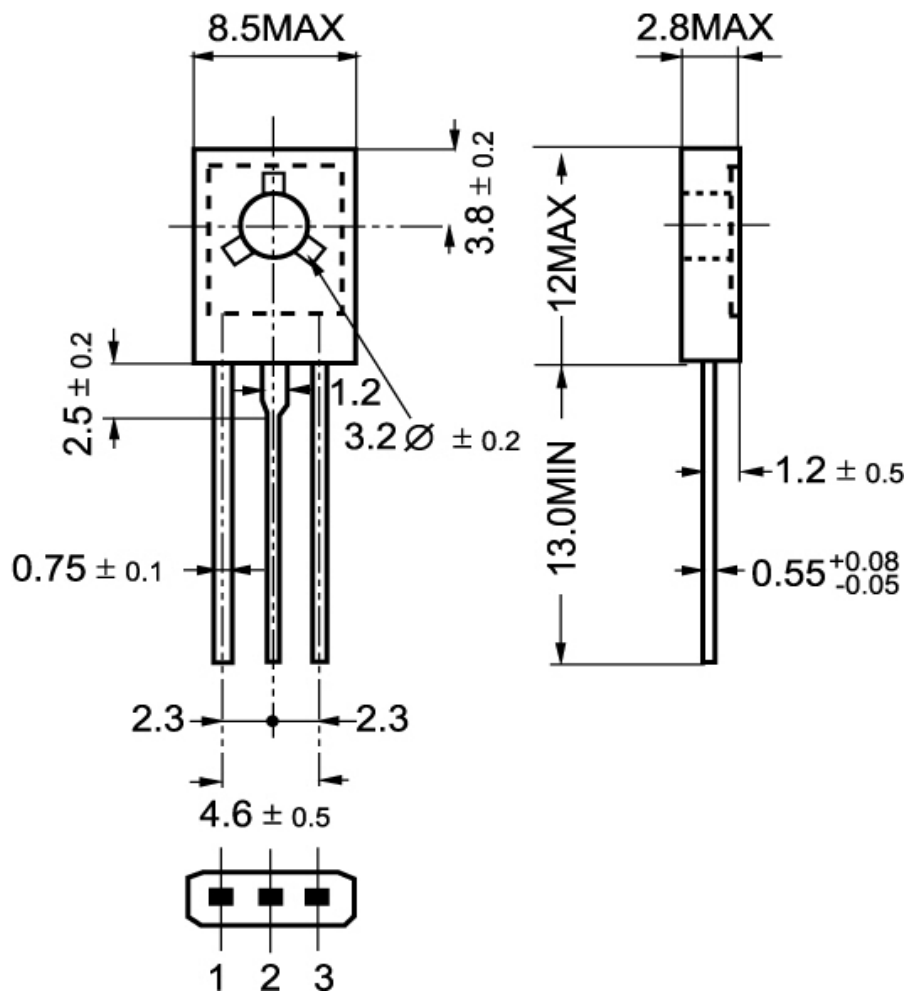
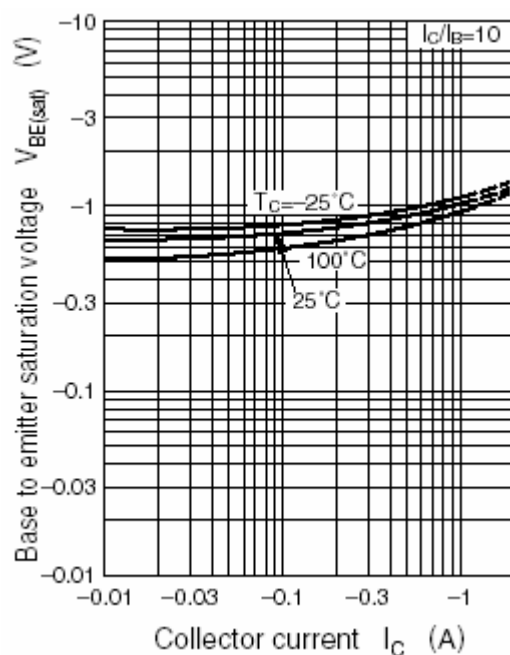
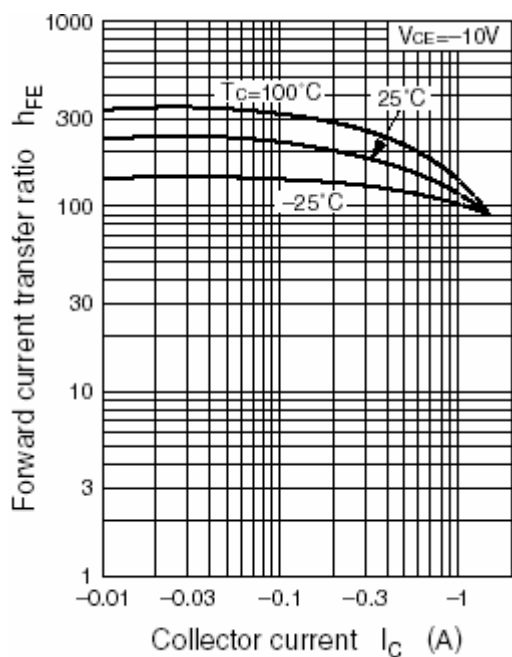
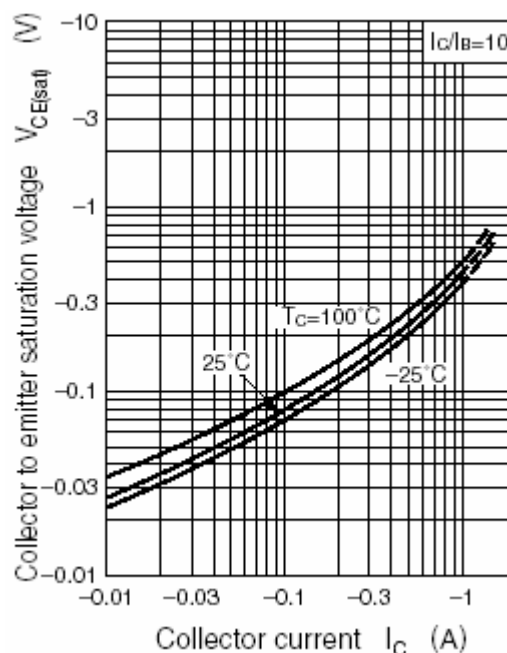
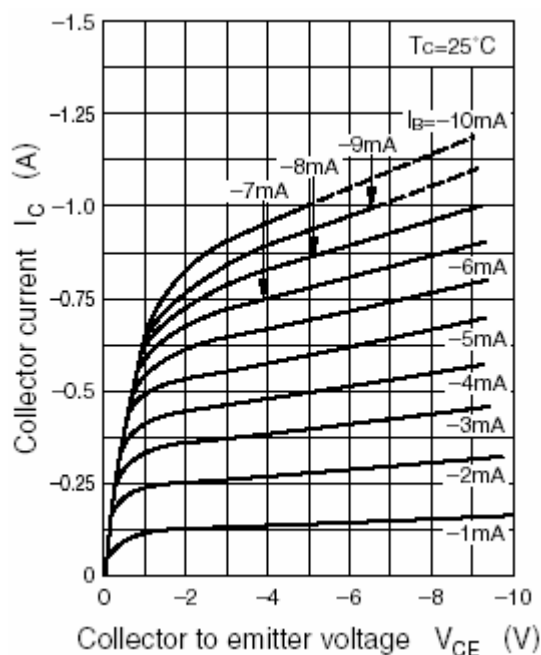


Fig.2 Outline dimensions

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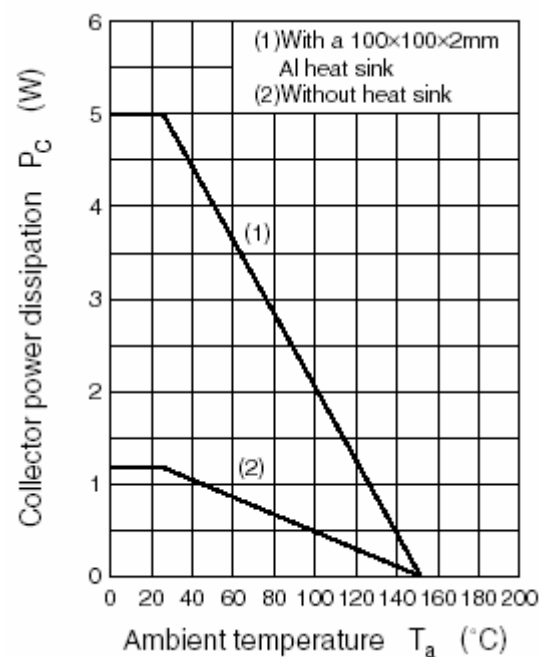


Fig.7 Power Derating

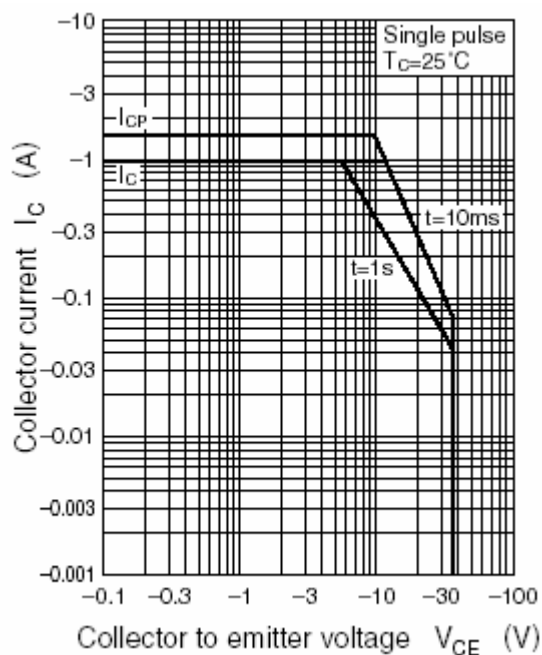


Fig.8 Safe Operating Area